

1N4148W

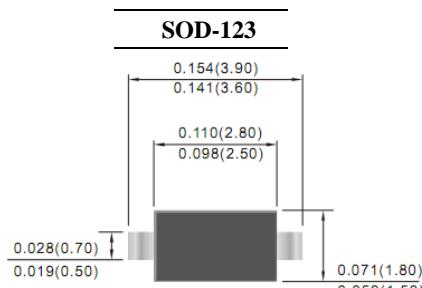
SWITCHING DIODE

FEATURES

- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

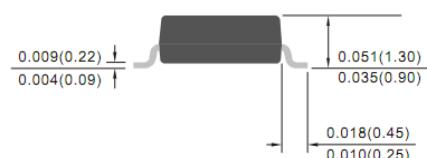
MECHANICAL DATA

- Case: SOD-123
- Terminals: Solderable per MIL-STD-750, Method 2026



Marking

Type number	Marking code
1N4148W	T4



Dimensions in inches and (millimeters)

Absolute Maximum Ratings at 25 °C

Parameter	Symbols	1N4148W	Units
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	100	V
Maximum RMS voltage	V _{RMS}	75	V
Continuous Forward Current	I _F	300	mA
Non-repetitive Peak Forward Surge Current at 1ms	I _{FSM}	4	A
Total Power Dissipation	P _{tot}	400	mW
Operating and Storage Temperature Range	T _j , T _{stg}	-55 ~ +150	°C

Characteristics at T_a = 25 °C

Parameter	Symbols	1N4148W	Units
Reverse Breakdown Voltage at I _R =1μA	V _{(BR)R}	75	V
Maximum Forward Voltage at 1 mA at 10 mA at 50 mA at 150 mA	V _F	0.715 0.855 1.00 1.25	V
Peak Reverse Current at V _R =20V T _j =25°C at V _R =75V T _j =25°C at V _R =25V T _j =150°C at V _R =75V T _j =150°C	I _R	0.025 1 30 50	μA
Typical Junction Capacitance	C _j	5	pF
Maximum Reverse Recovery Time ⁽¹⁾	t _{rr}	20	ns

(1) Measured with IF = 0.5 A, IR = 1 A, Irr = 0.25 A

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Fig.1 Forward Current Derating Curve

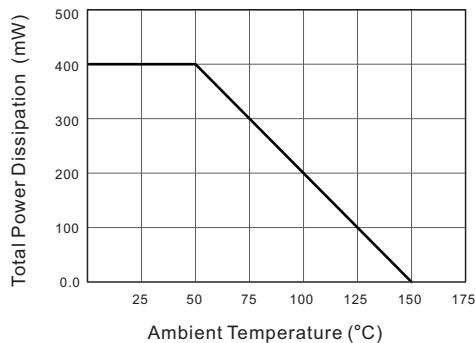


Fig.2 Typical Reverse Characteristics

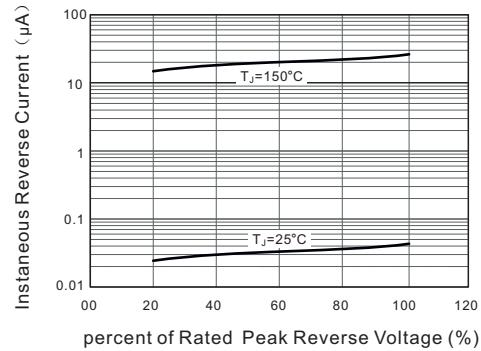


Fig.3 Typical Instaneous Forward Characteristics

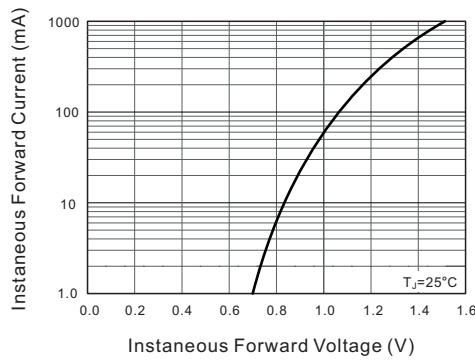


Fig.4 Typical Junction Capacitance

